

POWER & COMPOUND FAB REPORT TO 2024

FORECASTS – CAPACITIES – INVESTMENTS

GLOBAL FAB DATA ON POWER AND COMPOUND SEMICONDUCTORS

Driven by growing demand for 5G wireless communications, electric vehicles, green energy, data centers, biomedical, and both industrial and consumer IoT (Internet of Things) applications, power and compound fab investment and capacity are on the rise. Power electronics play a major role in harvesting the huge potential towards more efficient energy usage around the globe.

This report lists 957 facilities/lines worldwide which are operational from 2013 to 2024 including 47 new facilities and lines being added in 2021 or later.

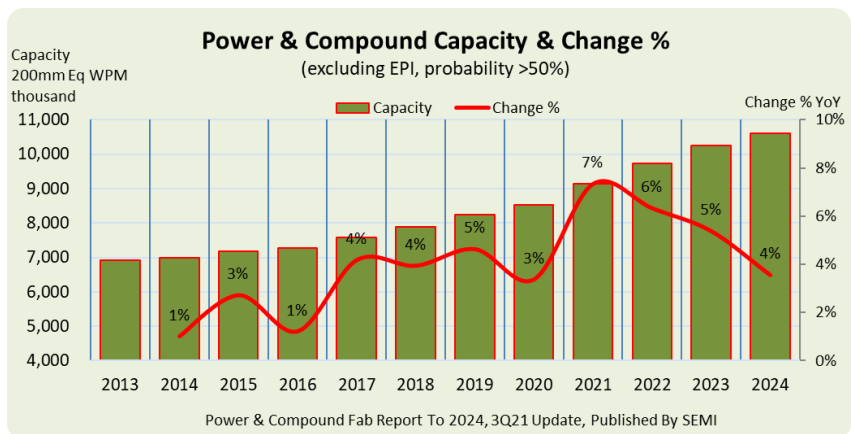
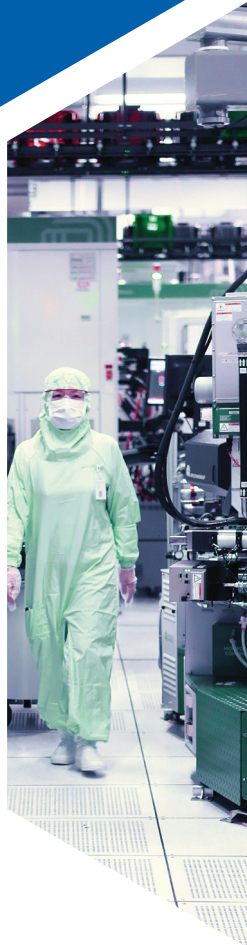
REPORT HIGHLIGHTS

- 12 consecutive years of fab data (2013-2024) in one Excel
- Company and fab information including fab status, greenfield projects, wafer size transitions, and more
- Construction and equipment investments by the quarter from past through 2024
- Technology highlights for Epitaxy, LED, IGBT, HEMT, MOSFET, BCD
- Materials information including SiC, Sapphire, GaN, GaAs, InP, III-V, and more

BENEFITS

- Stay up-to-date on current and future data trends in power and compound semiconductors
- Gain timely insights to identify new opportunities and customers
- Access to benchmark data used by financial institutions, industry experts, and top-tier companies worldwide

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DEVICE TYPES INCLUDE:

- Power Diode; Schottky Diode; Power MOSFET; Bipolar-CMOS-DMOS (BCD); Insulated-Gate Bipolar Transistor (IGBT); MOS-Controlled Thyristor (MCT); Integrated Gate-Commutated Thyristor (IGCT); Bipolar Junction Transistor (Bipolar Transistor or BJT)
- Silicon-Controlled Rectifier (SCR); Thyristor; Gate Turn-Off Thyristor (GTO); Triac; Bipolar Junction Transistor (BJT); Heterojunction Bipolar Transistor (HBT); High-Electron-Mobility Transistor (HEMT); also known as Heterostructure FET (HFET)
- Compound semiconductors include gallium arsenide (GaAs); gallium nitride (GaN); indium phosphide (InP); zinc selenide (ZnSe); zinc sulphide (ZnS); zinc selenide (ZnSe); silicon carbide (SiC); and silicon germanium (SiGe)

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| 2-3 users | \$4,750 | \$8,250 |
| 4+ users - Corporate License | \$12,500 | \$21,250 |

METHODOLOGY

The information for the fab reports and forecasts is compiled from various sources in the industry including publicly available information such as capital spending plans, fab plans, ramp schedules, and technology roadmaps. source data are verified across an extensive network of industry contacts. These data are used in modeling for each company and facility, incorporating various economic indicators and best educated estimates. The report uses a bottom-up approach, tracking projects per cleanroom facility but uses also a top down analysis by company, region, and industry segment. Content details include capital expenditure for construction and equipment, capacities, technologies used, product types, and wafer sizes.

HOW TO ORDER: <https://www.semi.org/en/products-services/purchase-market-reports>

APPLICABLE TO: Materials suppliers, Device manufacturers, Equipment suppliers, Supply Chain, Sales, Marketing, Executives

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